

MCM511000A • MCM51L1000A

AC OPERATING CONDITIONS AND CHARACTERISTICS

(VCC = 5.0 V ± 10%, TA = 0 to 70°C, Unless Otherwise Noted)

READ, WRITE, AND READ-MODIFY-WRITE CYCLES (See Notes 1, 2, 3, 4, and 5)

Parameter	Symbol		MCM511000A-70 MCM51L1000A-70		MCM511000A-80 MCM51L1000A-80		MCM511000A-10 MCM51L1000A-10		Unit	Notes
	Standard	Alternate	Min	Max	Min	Max	Min	Max		
Random Read or Write Cycle Time	t _{RELREL}	t _{RC}	130	—	150	—	180	—	ns	6
Read-Write Cycle Time	t _{RELREL}	t _{RWC}	155	—	175	—	210	—	ns	6
Page Mode Cycle Time	t _{CELCEL}	t _{PC}	40	—	45	—	55	—	ns	
Page Mode Read-Write Cycle Time	t _{CELCEL}	t _{PRWC}	65	—	70	—	85	—	ns	
Access Time from RAS	t _{RELOV}	t _{RAC}	—	70	—	80	—	100	ns	7, 8
Access Time from CAS	t _{CELOV}	t _{CAC}	—	20	—	20	—	25	ns	7, 9
Access Time from Column Address	t _{AVOV}	t _{AA}	—	35	—	40	—	50	ns	7, 10
Access Time from Precharge CAS	t _{CEHOV}	t _{CPA}	—	35	—	40	—	50	ns	7
CAS to Output in Low-Z	t _{CELOX}	t _{CLZ}	0	—	0	—	0	—	ns	7
Output Buffer and Turn-Off Delay	t _{CEHOZ}	t _{OFF}	0	20	0	20	0	20	ns	11
Transition Time (Rise and Fall)	t _T	t _T	3	50	3	50	3	50	ns	
RAS Precharge Time	t _{REHREL}	t _{RP}	50	—	60	—	70	—	ns	
RAS Pulse Width	t _{RELREH}	t _{RAS}	70	10,000	80	10,000	100	10,000	ns	
RAS Pulse Width (Fast Page Mode)	t _{RELREH}	t _{RASP}	70	100,000	80	100,000	100	100,000	ns	
RAS Hold Time	t _{CELREH}	t _{RSH}	20	—	20	—	25	—	ns	
CAS Hold Time	t _{RELCEH}	t _{CSH}	70	—	80	—	100	—	ns	
CAS Pulse Width	t _{CELCEH}	t _{CAS}	20	10,000	20	10,000	25	10,000	ns	
RAS to CAS Delay Time	t _{RELCEL}	t _{RCD}	20	50	20	60	25	75	ns	12
RAS to Column Address Delay Time	t _{RELAV}	t _{RAD}	15	35	15	40	20	50	ns	13
CAS to RAS Precharge Time	t _{CEHREL}	t _{CRP}	5	—	5	—	5	—	ns	
CAS Precharge Time (Page Mode Cycle Only)	t _{CEHCEL}	t _{CP}	10	—	10	—	10	—	ns	
Row Address Setup Time	t _{AVREL}	t _{ASR}	0	—	0	—	0	—	ns	
Row Address Hold Time	t _{RELAX}	t _{RAH}	10	—	10	—	15	—	ns	
Column Address Setup Time	t _{AVCEL}	t _{ASC}	0	—	0	—	0	—	ns	
Column Address Hold Time	t _{CELAX}	t _{CAH}	15	—	15	—	20	—	ns	
Column Address Hold Time Referenced to RAS	t _{RELAX}	t _{AR}	55	—	60	—	75	—	ns	
Column Address to RAS Lead Time	t _{AVREH}	t _{RAL}	35	—	40	—	50	—	ns	

(continued)

NOTES:

1. V_{IH} min and V_{IL} max are reference levels for measuring timing of input signals. Transition times are measured between V_{IH} and V_{IL}.
2. An initial pause of 200 μs is required after power-up followed by 8 RAS cycles before proper device operation is guaranteed.
3. The transition time specification applies for all input signals. In addition to meeting the transition rate specification, all input signals must transmit between V_{IH} and V_{IL} (or between V_{IL} and V_{IH}) in a monotonic manner.
4. AC measurements t_T = 5.0 ns.
5. TF pin must be at V_{IL} or open if not used.
6. The specifications for t_{RC} (min) and t_{RWC} (min) are used only to indicate cycle time at which proper operation over the full temperature range (0°C ≤ T_A ≤ 70°C) is assured.
7. Measured with a current load equivalent to 2 TTL (−200 μA, +4 mA) loads and 100 pF with the data output trip points set at V_{OH} = 2.0 V and V_{OL} = 0.8 V.
8. Assumes that t_{RCD} ≤ t_{RCD} (max).
9. Assumes that t_{RCD} ≥ t_{RCD} (max).
10. Assumes that t_{RAD} ≥ t_{RAD} (max).
11. t_{OFF} (max) defines the time at which the output achieves the open circuit condition and is not referenced to output voltage levels.
12. Operation within the t_{RCD} (max) limit ensures that t_{RAC} (max) can be met. t_{RCD} (max) is specified as a reference point only; if t_{RCD} is greater than the specified t_{RCD} (max) limit, then access time is controlled exclusively by t_{CAC}.
13. Operation within the t_{RAD} (max) limit ensures that t_{RAC} (max) can be met. t_{RAD} (max) is specified as a reference point only; if t_{RAD} is greater than the specified t_{RAD} (max), then access time is controlled exclusively by t_{AA}.